

**In the Claims:**

Please amend claim 1 by rewriting the same as follows:

1. A semiconductor device comprising:

a semiconductor substrate; and

a gate insulating film provided on said semiconductor substrate, at least a part of said gate insulating film including an insulating film containing metal, silicon and oxygen;

wherein at least one of fluorine and nitrogen is contained in said insulating film containing metal, silicon and oxygen.

**REMARKS**

This amendment is submitted prior to an examination of the above-identified application. Claims 1-20 are pending in the application.

Claim 1 has been amended for clarification. Attached hereto is a marked-up version of the changes made to claim 1 by the current amendment. The attached page is captioned "**Version with Markings to Show Changes Made.**" It is submitted that claim 1, as originally presented, is patentably distinct over prior art, and that claim 1 was in full compliance with the requirements of 35 U.S.C. §112. Changes to claim 1, as presented herein, are not made for the purpose of patentability within the meaning of 35 U.S.C. §§101, 102, 103 or 112. Rather, these changes are made simply for clarification and to round out the scope of protection to which Applicants are entitled. Applicants reserve the right to pursue any and all cancelled subject matter without prejudice, admission, surrender or any intention to create any estoppel as to equivalence.